



42390.P7511

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
Ali Keshavarzi et al. )  
Application No.: 09/469,406 )  
Filed: December 22, 1999 )  
For: DECOUPLING CAPACITORS FOR THIN )  
GATE OXIDES )  
Assignee: Intel Corporation )

Examiner: Donghee Kang

Art Unit: 2811

*I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on:*

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R. P. Lee 11-17-03  
Signature Date

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

RESPONSE

Sir:

This is in response to the non-final Office action dated August 15, 2003. Reconsideration of the application is requested. The application is not amended in this response.

REMARKS

Claims 29-50 are in the application of which claims 29 and 40 are in independent form. Claims 29-31, 35-36, 38-42, 46-47, and 49-50 are rejected and claims 32-34, 37, 43-45, and 48 are objected to.

Claims 29-31, 35-36, 38-42, 46-47 & 49-50 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Manning et al. (US 5,962,887). For the following reasons, the rejections should be withdrawn.

The rejection heading does not refer to the admitted prior art (APA) FIGS. 1 and 9, but the explanation of the rejection in the Office action does refer to the APA. The APA is relied by the Office action, pp. 2 and 3, to show that diffusion regions could be formed in the device body. Applicants admit that diffusion regions are well known in the technology. The Office action, pp.

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